



FP120F60ADNS1

主要参数 MAIN CHARACTERISTICS

$I_F(AV)$	60*2 A
V_{RRM}	600 V
$V_F(typ)$	1.6 V
$t_{rr} (typ)$	48ns

用途

- UPS
- PFC
- 逆变焊机
- 光伏逆变

APPLICATIONS

- UPS
- PFC
- Inversion Welder
- Solar inverter

产品特性

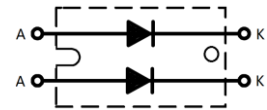
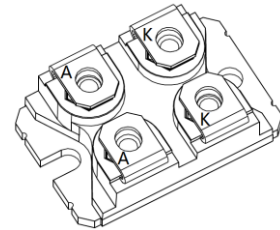
- 平面钝化芯片
- 低功耗，高效率
- 短恢复时间
- 软恢复特性

FEATURES

- Planar passivated chips
- Low power loss, high efficiency
- Very short recovery time
- Soft Recovery Characteristics

封装 Package

SOT-227



订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package	包装 Packaging	器件重量 Device Weight
FP120F60ADNS1-NS1-BR	FP120F60ADNS1	SOT-227	条管	165g





绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}	600	V
正向平均整流电流 Average forward Current T _C =100℃	$I_{F(AV)}$	120	A
		60	
峰值单脉冲浪涌电流 Peak one Cycle Surge Forward Current(Non-Repetitive) t=8.3ms	I_{FSM}	480	A
结温 Junction Temperature	T_j	-50~+150	℃
储存温度 Storage temperature range	T_{STG}	-50~+150	℃

电特性 ELECTRICAL CHARACTERISTICS (Tc=25℃ PER DIODE)

项 目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单位 Unit
V _R	I _R =50μA		600	-	-	V
I _R	T _j =25℃	V _R =V _{RRM}	-	-	10	μA
	T _j =125℃		-	-	800	μA
V _F	T _j =25℃	I _F =60A	-	1.8	2.2	V
	T _j =125℃		-	1.5	2.0	V
trr	I _F =0.5A, I _R =1A, I _{RR} =0.25A		-	48	55	ns
trr	I _F =1A, V _R =30V, di _F /dt=-100A/μs		-	-	45	ns
trr	I _F =60A, V _R =200V, di _F /dt=-200A/μs T _c =25℃		-	27	-	ns
Q _{rr}			-	33	-	nc
I _{RRM}			-	1.5	-	A
trr	I _F =60A, V _R =200V, di _F /dt=-200A/μs T _c =125℃		-	91	-	ns
Q _{rr}			-	173	-	nc
I _{RRM}			-	3.8	-	A

热特性 THERMAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	最大值 Value(max)	单 位 Unit
结到管壳的热阻 Thermal resistance from junction to case	$R_{th(j-c)}$	0.6	℃/W





特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Fig.1 TYPICAL FORWARD CHARACTERISTICS

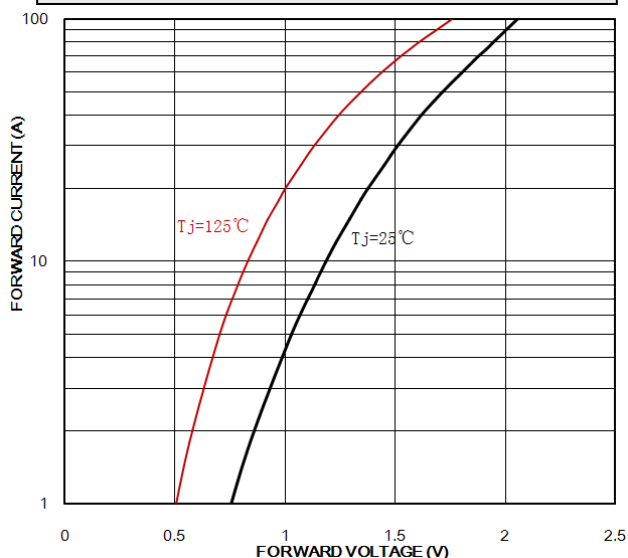


Fig.2 TYPICAL REVERSE CHARACTERISTICS

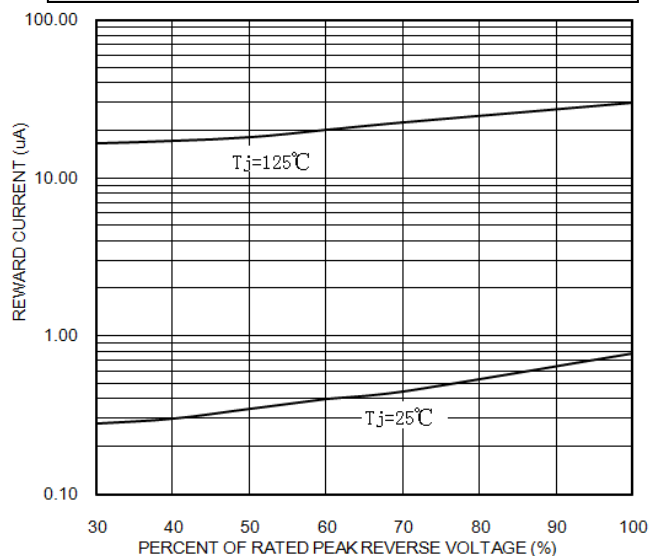


Fig.3 TYPICAL JUNCTION CAPACITANCE

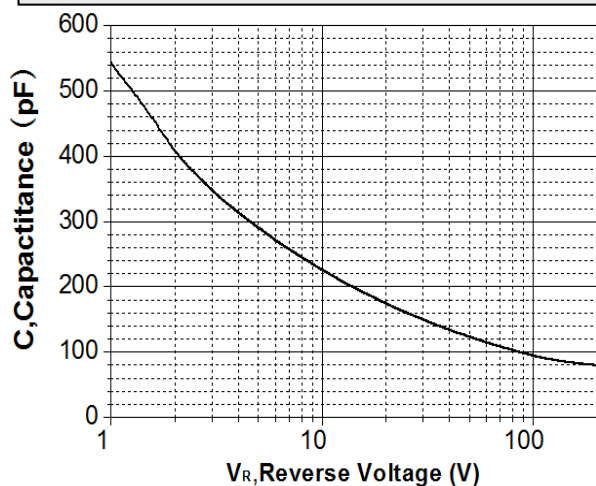


Fig.4 Reverse recovery time versus di/dt

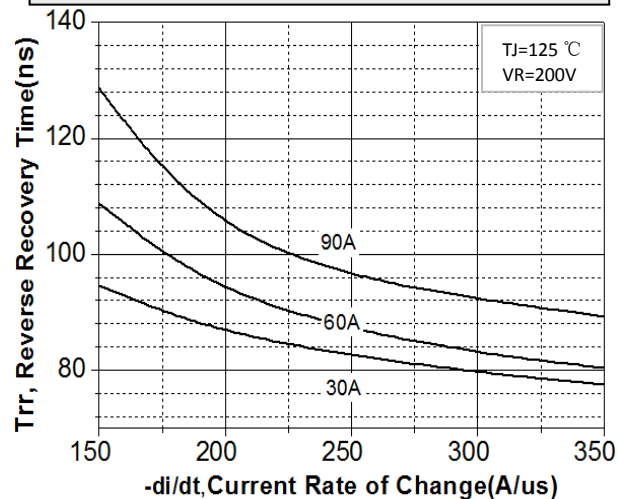


Fig.5 Reverse recovery charges versus di/dt

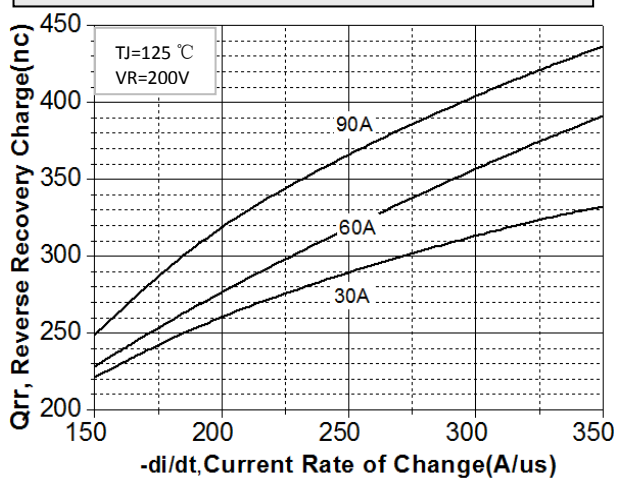
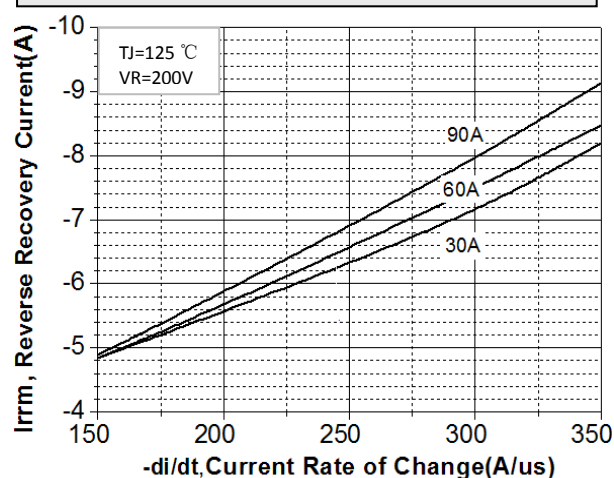


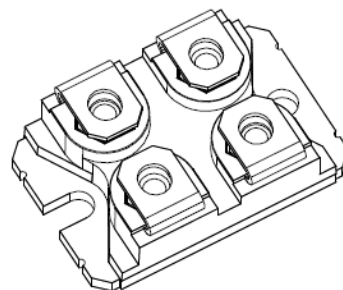
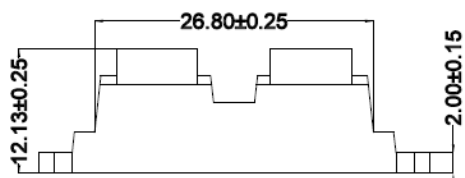
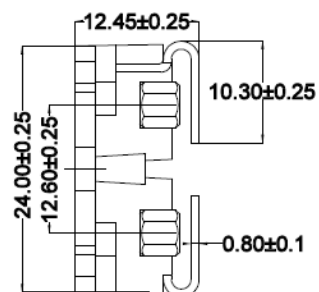
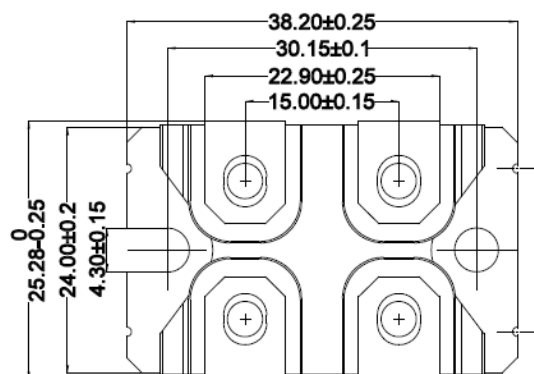
Fig.6 Peak reverse recovery current versus di/dt





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单位 Unit : mm





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